Power MOSFET

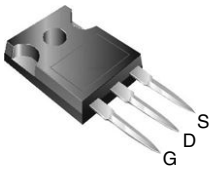
PRODUCT SUMMARY		
V_{DS} (V) at T_J max.	650 V	
$R_{DS(on)}$ (Ω)	V_{GS} = 10 V	0.07
Q_g (Max.) (nC)	216	
Q_{gs} (nC)	39	
Q_{gd} (nC)	57	
Configuration	Single	

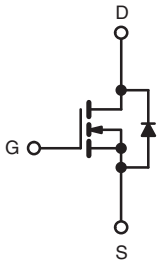
FEATURES

- Low Figure-of-Merit R_{on} x Q_g
- 100 % Avalanche Tested
- Gate Charge Improved
- Lowest $R_{DS(on)}$ for TO-247AC Package
- Compliant to RoHS Directive 2002/95/EC

Available
RoHS* COMPLIANT

TO-247AC





N-Channel MOSFET

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free	SiHG47N60S-E3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	600	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	V_{GS} at 10 V	T_C = 25 °C	I_D	47	A
		T_C = 100 °C		30	
Pulsed Drain Current[a]			I_{DM}	140	
Linear Derating Factor				3.3	W/°C
Single Pulse Avalanche Energy[b]			E_{AS}	1800	mJ
Maximum Power Dissipation			P_D	417	W
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)[c]	for 10 s			300	

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature.
b. V_{DD} = 50 V, starting T_J = 25 °C, L = 73.5 mH, R_g = 25 Ω, I_{AS} = 7 A.
c. 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.3	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA		-	0.7	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 600 V, V_{GS} = 0 V		-	-	1	µA
		V_{DS} = 600 V, V_{GS} = 0 V, T_J = 150 °C		-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 30 A	-	0.057	0.07	Ω
Forward Transconductance[a]	g_{fs}	V_{DS} = 8 V, I_D = 3 A		-	7.5	-	S
Dynamic							
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 100 V, f = 1.0 MHz		-	6630	-	pF
Output Capacitance	C_{oss}			-	220	-	
Reverse Transfer Capacitance	C_{rss}			-	7	-	
Total Gate Charge	Q_g	V_{GS} = 10 V	I_D = 20 A, V_{DS} = 400 V	-	180	216	nC
Gate-Source Charge	Q_{gs}			-	39	-	
Gate-Drain Charge	Q_{gd}			-	57	-	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 380 V, I_D = 47 A, R_g = 4.4 Ω, V_{GS} = 13 V		-	30	-	ns
Rise Time	t_r			-	12	-	
Turn-Off Delay Time	$t_{d(off)}$			-	115	-	
Fall Time	t_f			-	9	-	
Gate Input Resistance	R_g	f = 1 MHz, open drain		-	0.62	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	47	A
Pulsed Diode Forward Current	I_{SM}			-	-	140	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = 47 A, V_{GS} = 0 V		-	-	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = I_S, dI/dt = 100 A/µs, V_R = 25 V		-	750	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	18	-	µC
Body Diode Reverse Recovery Current	I_{RRM}			-	39	-	A

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

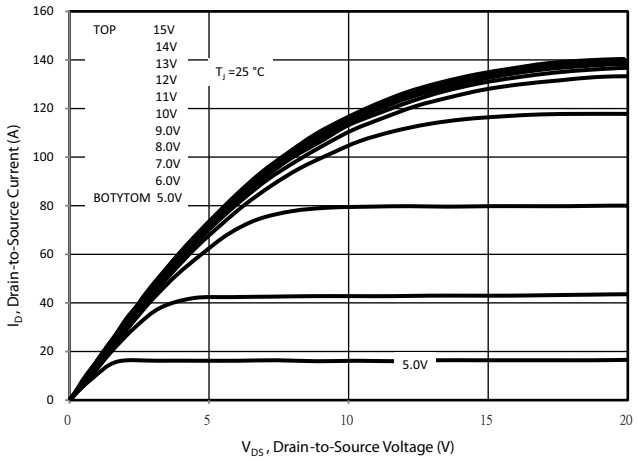


Fig. 1 - Typical Output Characteristics (TO-247)

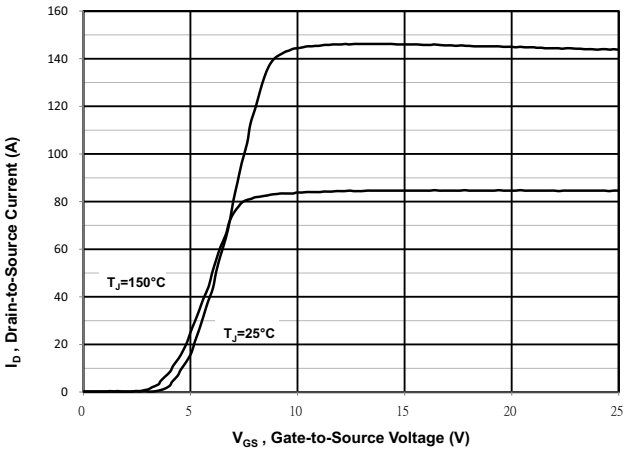


Fig. 3 - Typical Transfer Characteristics

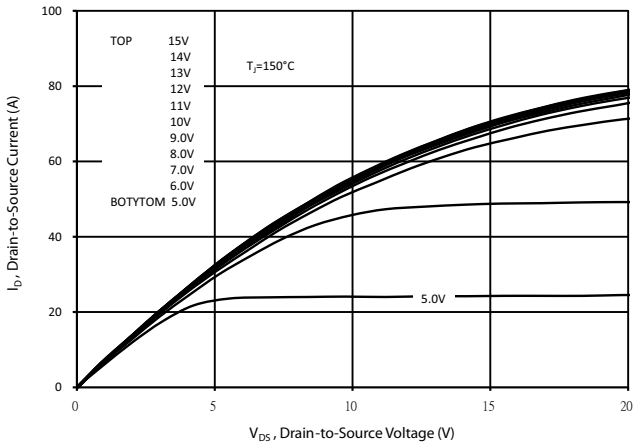


Fig. 2 - Typical Output Characteristics (TO-247)

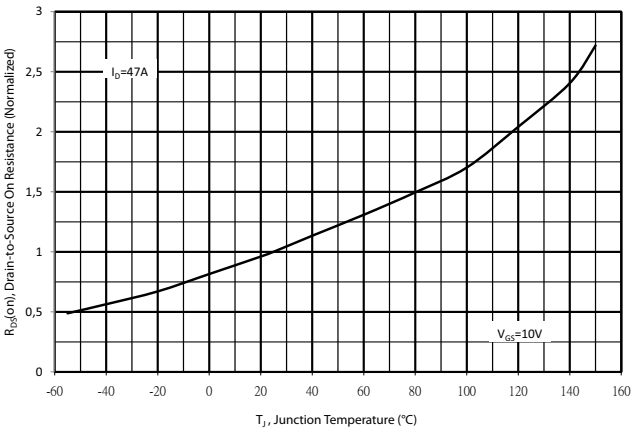


Fig. 4 - Normalized On-Resistance vs. Temperature

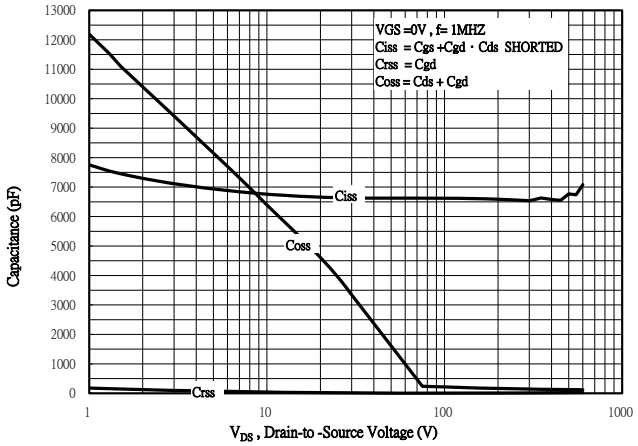


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

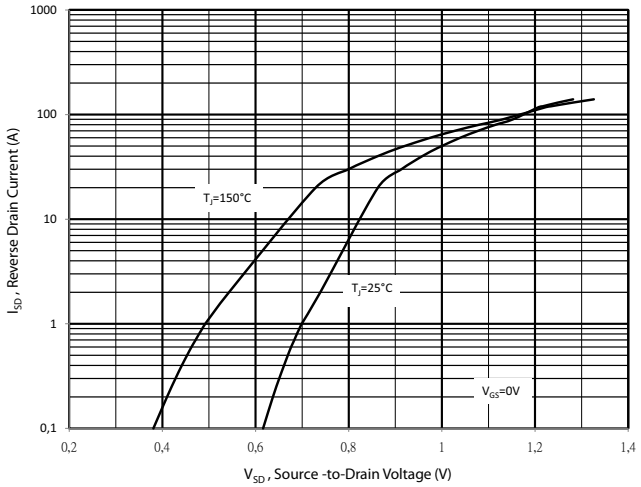


Fig. 7 - Typical Source-Drain Diode Forward Voltage

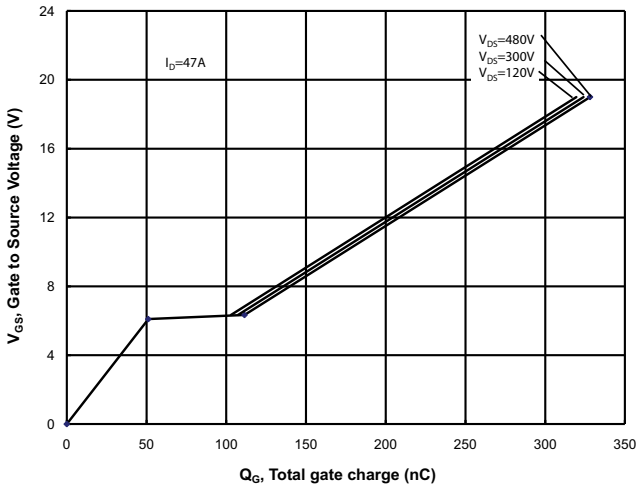


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

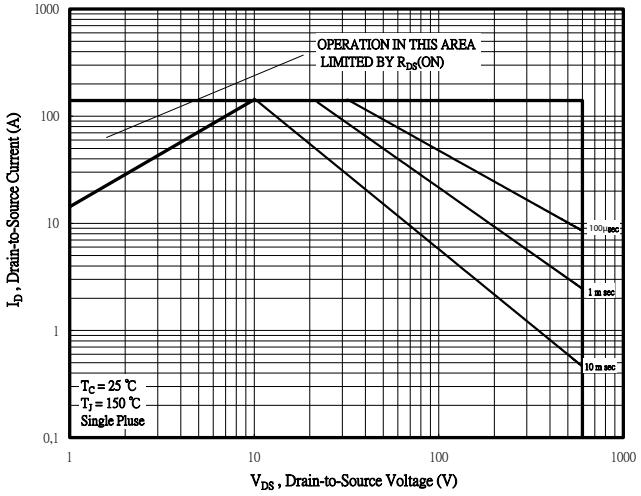


Fig. 8 - Maximum Safe Operating Area

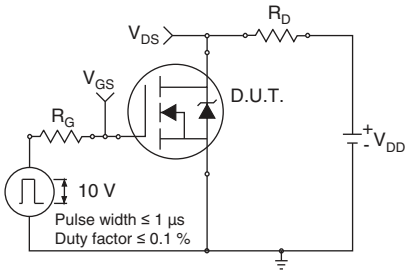


Fig. 9a - Switching Time Test Circuit

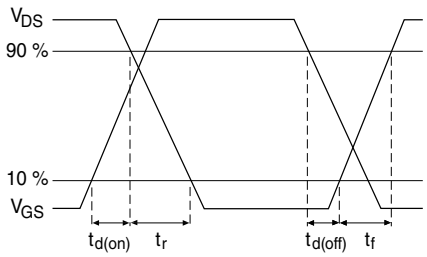


Fig. 9b - Switching Time Waveforms

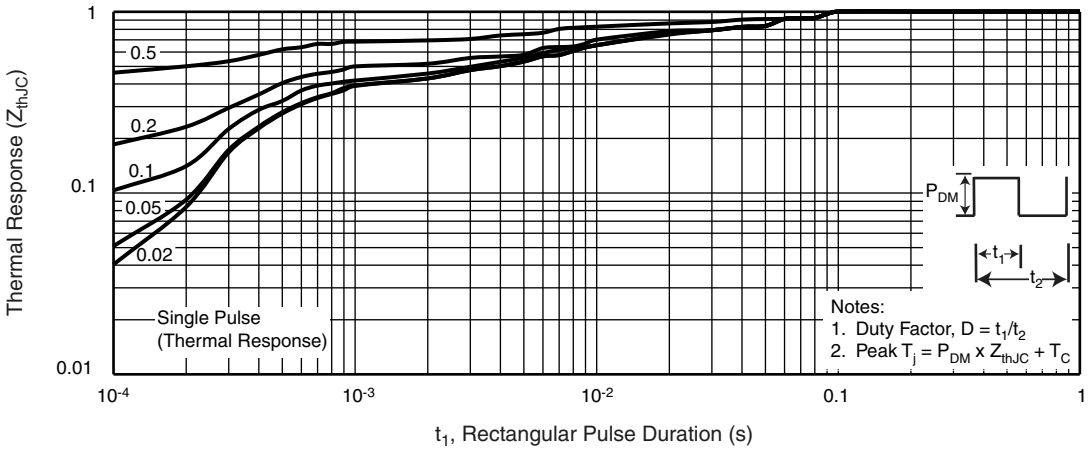


Fig. 10 - Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-247AC)

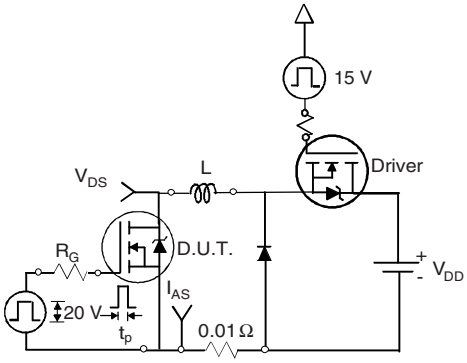


Fig. 11a - Unclamped Inductive Test Circuit

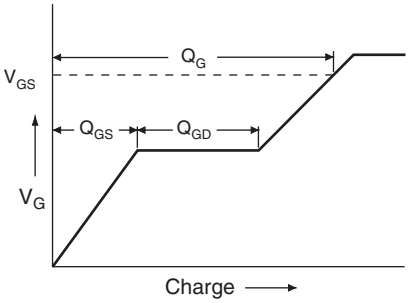


Fig. 12a - Basic Gate Charge Waveform

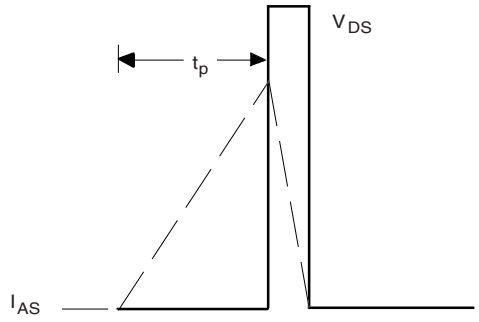


Fig. 11b - Unclamped Inductive Waveforms

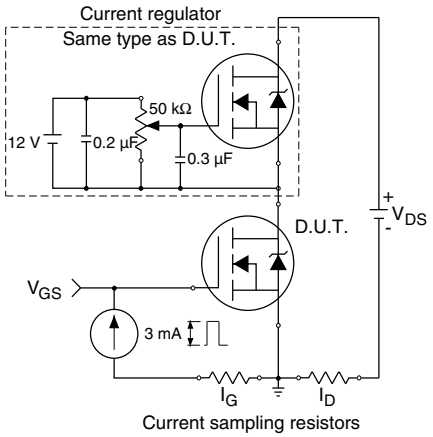
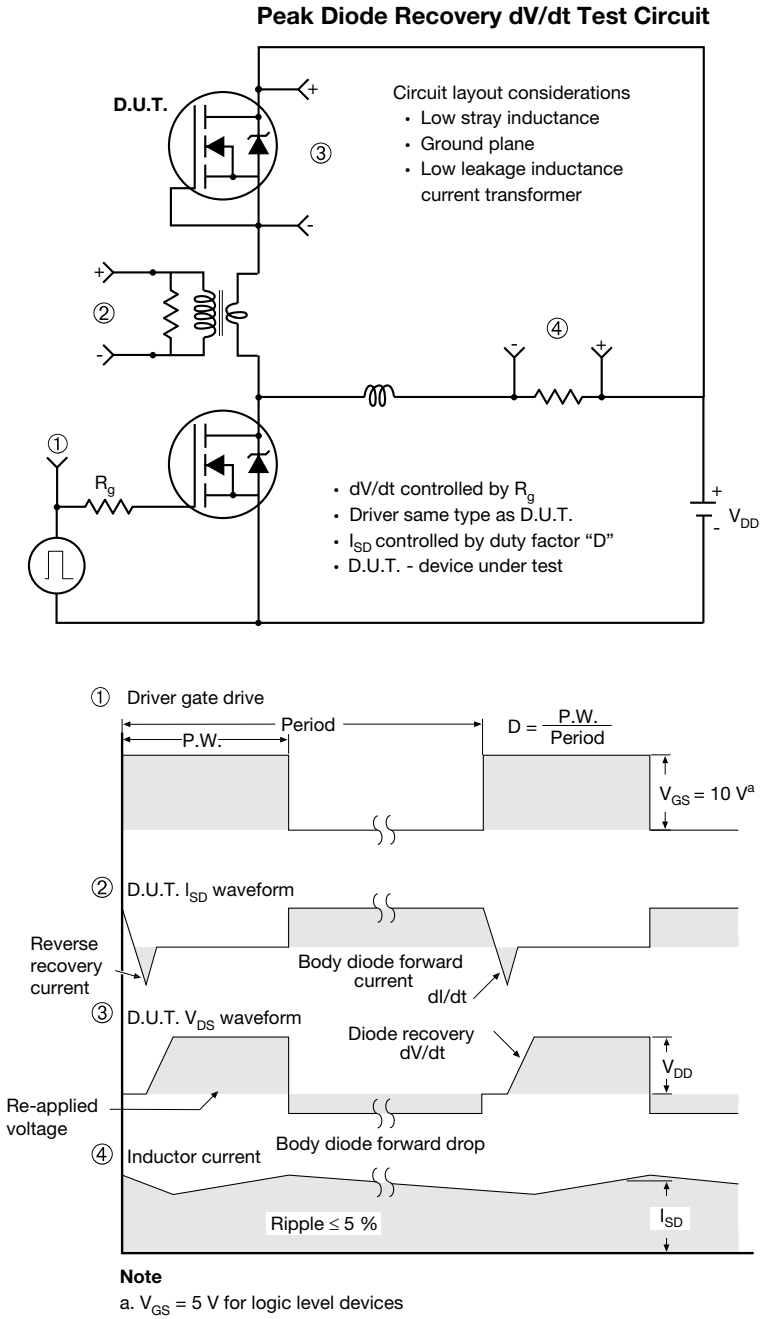


Fig. 12b - Gate Charge Test Circuit



Note

a. V_{GS} = 5 V for logic level devices

Fig. 13 - For N-Channel

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